

MOSFET Maximum Ratings T_J = 25°C unless otherwise noted.

Symbol	Parameter		Ratings	Units	
V _{DSS}	Drain-to-Source Voltage		80	V	
V _{GS}	Gate-to-Source Voltage		±20	V	
I _D	Drain Current - Continuous (V _{GS} =10) (Note 1)	T _C =25°C	110	Α	
	Pulsed Drain Current	T _C = 25°C	See Figure 4		
E _{AS}	Single Pulse Avalanche Energy	(Note 2)	512	mJ	
P _D	Power Dissipation		300	W	
	Derate Above 25°C		2.0	W/ºC	
T _J , T _{STG}	Operating and Storage Temperature		-55 to + 175	°C	
R _{0JC}	Thermal Resistance, Junction to Case		0.5	°C/W	
R _{0JA}	Maximum Thermal Resistance, Junction to Ambient	(Note 3)	43	°C/W	

Notes:

1: Current is limited by bondwire configuration.

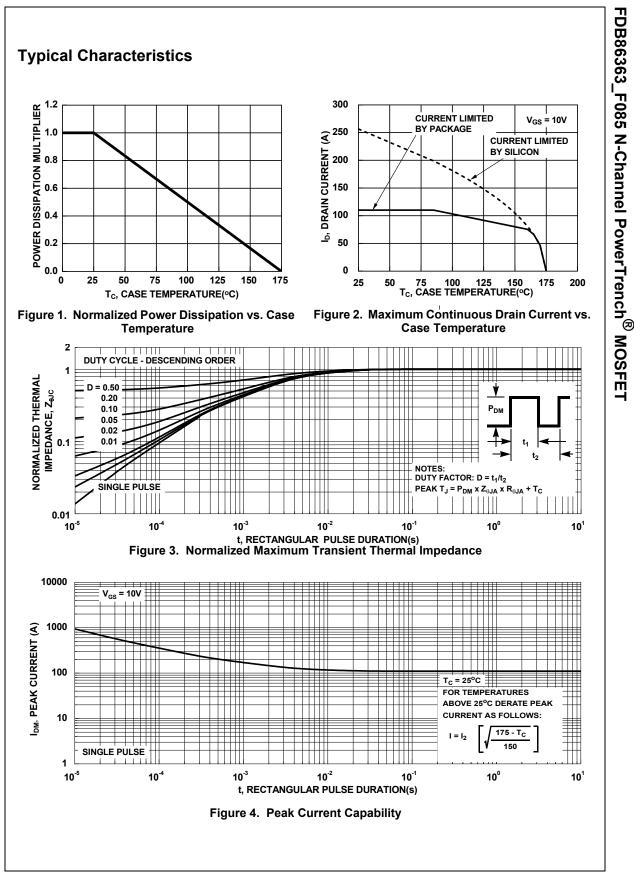
2: Starting $T_J = 25^{\circ}$ C, L = 0.25mH, $I_{AS} = 64A$, $V_{DD} = 80V$ during inductor charging and $V_{DD} = 0V$ during time in avalanche.

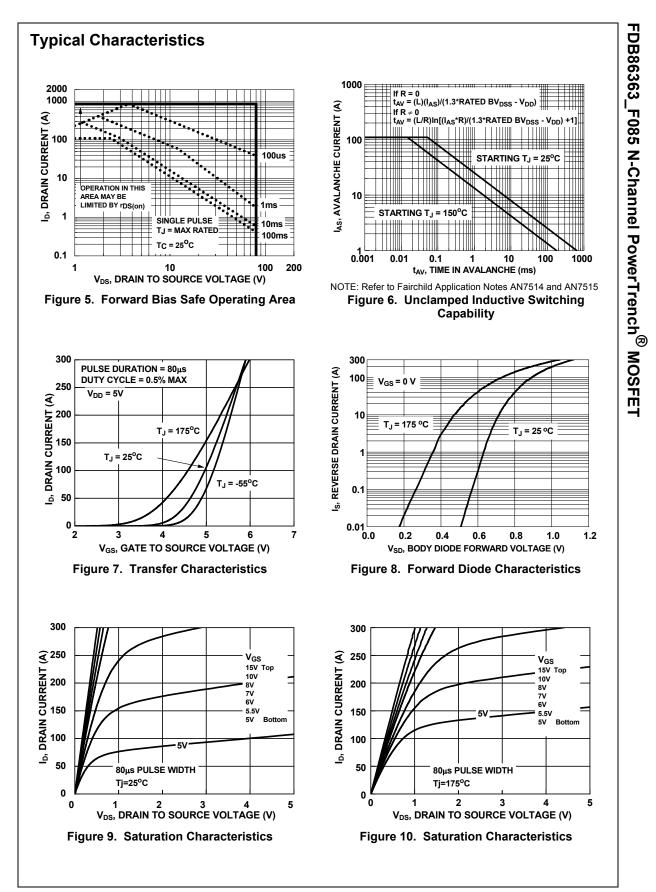
3: R_{0JA} is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{0JC} is guaranteed by design, while R_{0JA} is determined by the board design. The maximum rating presented here is based on mounting on a 1 in² pad of 2oz copper.

Package Marking and Ordering Information

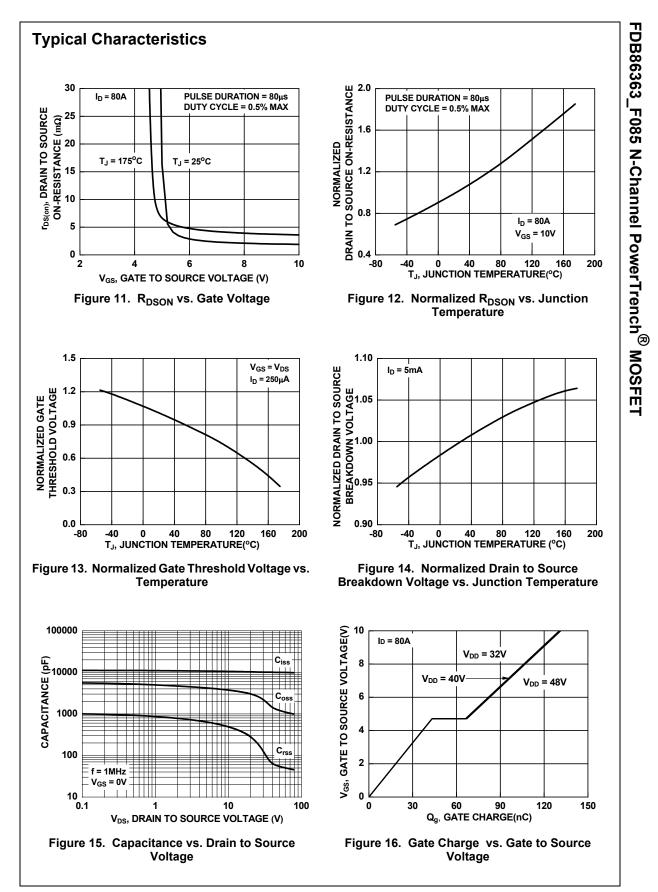
Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDB86363	FDB86363_F085	D2-PAK(TO-263)	330mm	24mm	800 units

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Units
Off Cha	racteristics			I			
B _{VDSS}	Drain-to-Source Breakdown Voltage	I _D = 250μA, \	/ _{GS} = 0V	80	-	-	V
		V _{DS} =80V,		-	-	1	μA
IDSS	Drain-to-Source Leakage Current	-	$T_{\rm J} = 175^{\rm o}C$ (Note 4)	-	-	1	mA
I _{GSS}	Gate-to-Source Leakage Current	$V_{GS} = \pm 20V$		-	-	±100	nA
On Cha	racteristics						
V _{GS(th)}	Gate to Source Threshold Voltage	V_{GS} = V_{DS} , I	_D = 250μA	2.0	3.0	4.0	V
	Drain to Source On Resistance	I _D = 80A,	T _J = 25 ^o C	-	2.0	2.4	mΩ
R _{DS(on)}	Drain to Source On Resistance	V_{GS} = 10V T _J = 175 ^o C (Note 4)		-	3.8	4.3	mΩ
C _{iss}	Input Capacitance	V _{DS} = 40V, V _{GS} = 0V, f = 1MHz f = 1MHz		-	10000	-	pF
C _{oss}	Output Capacitance			-	1400	-	pF
C _{rss}	Reverse Transfer Capacitance			-	95	-	pF
R _g	Gate Resistance			-	3.3	-	Ω
Q _{g(ToT)}	Total Gate Charge at 10V	V_{GS} = 0 to 10	• 00 • •	-	131	150	nC
Q _{g(th)}	Threshold Gate Charge	$V_{GS} = 0 \text{ to } 2V$ $I_D = 80A$		-	18	21	nC
Q _{gs}	Gate-to-Source Gate Charge			-	47	-	nC
Q _{gd}	Gate-to-Drain "Miller" Charge			-	24	-	nC
	ng Characteristics			_	_	231	ns
t _{on} t _{d(on)}	Turn-On Delay			-	38	-	ns
t _r	Rise Time	V _{DD} = 40V, I	_D = 80A.	-	129	-	ns
d(off)	Turn-Off Delay	V_{GS} = 10V, R_{GEN} = 6 Ω		-	64	-	ns
f	Fall Time			-	40	-	ns
t _{off}	Turn-Off Time			-	-	135	ns
Drain-S	ource Diode Characteristics				· · ·		
V _{SD}	Source-to-Drain Diode Voltage	I_{SD} =80A, V_{GS} = 0V I_{SD} = 40A, V_{GS} = 0V		-	-	1.25	V
• SD				-	-	1.2	V
t _{rr}	Reverse-Recovery Time	$I_{F} = 80A, dI_{SD}/dt = 100A/\mu s,$		-	88	101	ns
Q _{rr}	Reverse-Recovery Charge	V _{DD} =64V		-	129	157	nC





FDB86363_F085 Rev. C2



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Freinnindry		notice to improve design.
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